

SUM110N06-3m4L

Vishay Siliconix

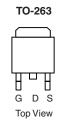
N-Channel 60-V (D-S) 175 °C MOSFET

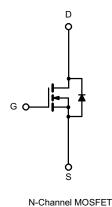
PRODUCT SUMMARY				
V _{(BR)DSS} (V)	r _{DS(on)} (Ω)	I _D (A)		
60	0.0034 at V _{GS} = 10 V	1108		
	0.0041 at V _{GS} = 4.5 V	110 ^a		

FEATURES

- TrenchFET[®] Power MOSFET
- 100 % R_g Tested







Ordering Information: SUM110N06-3m4L-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS T_A	= 25 °C, unless other	wise noted			
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	60	v	
Gate-Source Voltage		V _{GS} ±	± 20	v	
Continuous Drain Current (T _J = 175 °C)	T _C = 25 °C	I _D	110 ^a	А	
	T _C = 125 °C	D'D	110 ^a		
Pulsed Drain Current		I _{DM}	440		
Avalanche Current, Single Pulse		I _{AS}	75		
Avalanche Energy, Single Pulse	L = 0.1 mH	E _{AS}	280	mJ	
	T _C = 25 °C	В	375 ^b	14/	
Maximum Power Dissipation	T _A = 25 °C ^c	P _D –	3.75	W	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Unit	
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)		R _{thJC}	0.4	0/10	

Notes:

a. Package limited.

b. See SOA curve for voltage derating.

c. When Mounted on 1" square PCB (FR-4 material).

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 V, I_D = 250 \mu A$	60			v	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1		3	v	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1	μΑ	
		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$			50		
		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, \text{ T}_{\text{J}} = 175 ^{\circ}\text{C}$			10	mA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	120			А	
Drain-Source On-State Resistance ^a		V _{GS} = 10 V, I _D = 30 A		0.0028	0.0034		
	r	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		0.0033	0.0041		
	^r DS(on)	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 30 \text{ A}, \text{ T}_{J} = 125 ^{\circ}\text{C}$			0.0055	Ω	
		V_{GS} = 10 V, I _D = 30 A, T _J = 175 °C			0.007		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 30 A	30			S	
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		12900		pF	
Output Capacitance	C _{oss}			1060			
Reverse Transfer Capacitance	C _{rss}			700			
Total Gate Charge ^c	Qg			200	300	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 30$ V, $V_{GS} = 10$ V, $I_{D} = 110$ A		50			
Gate-Drain Charge ^c	Q _{gd}			33			
Gate Resistance	Rg	f = 1.0 MHz	0.65	1.3	2	Ω	
Turn-On Delay Time ^c	t _{d(on)}			22	35		
Rise Time ^c	t _r	$V_{DD} = 30 \text{ V}, \text{ R}_{\text{L}} = 0.4 \Omega$ $\text{I}_{\text{D}} \cong 110 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 2.5 \Omega$		130	200	ns	
Turn-Off Delay Time ^c	t _{d(off)}			110	165		
Fall Time ^c	t _f			280	420		
Source-Drain Diode Ratings and Cha	aracteristics 7	_C = 25 °C ^b					
Continuous Current	ا _S				110	•	
Pulsed Current	I _{SM}	1 1			440	A	
Forward Voltage ^a	V _{SD}	I _F = 110 A, V _{GS} = 0 V		1.0	1.5	V	
Reverse Recovery Time	t _{rr}			55	82	ns	
Peak Reverse Recovery Charge	I _{RM(REC)}	I _F = 110 A, di/dt = 100 A/μs		3.6	5.4	А	
Reverse Recovery Charge	Q _{rr}			0.1	0.22	μC	

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

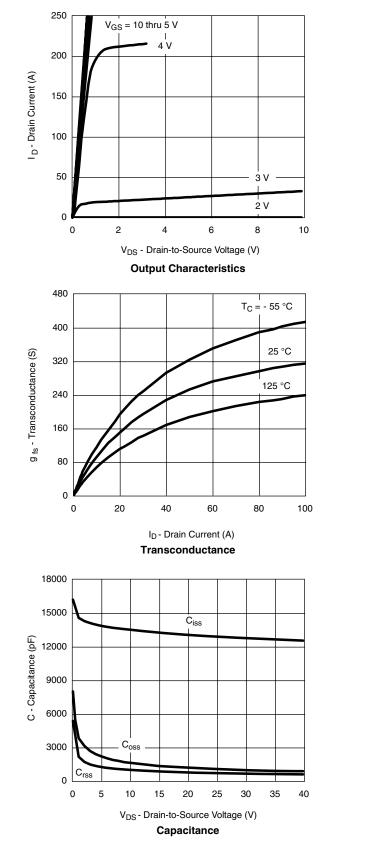
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

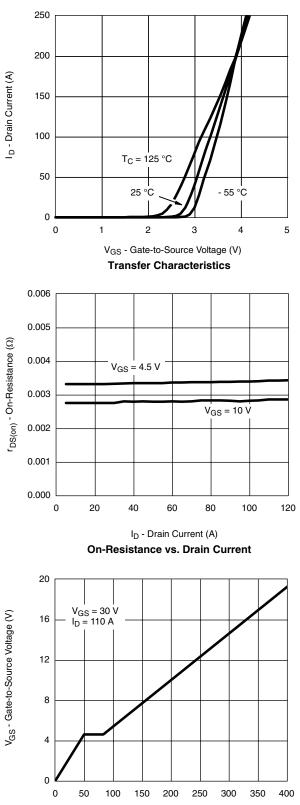


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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



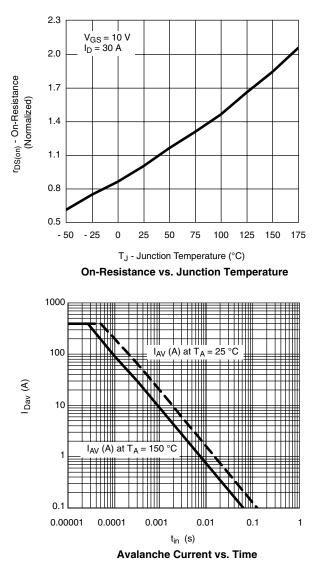


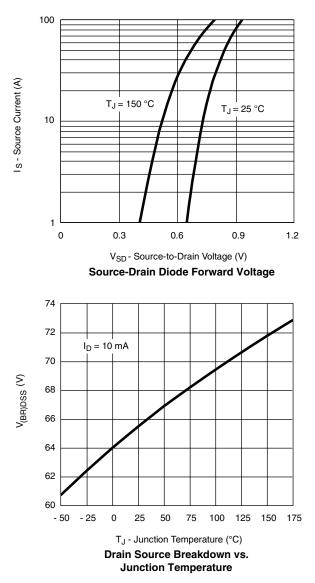
Qg - Total Gate Charge (nC)

Gate Charge

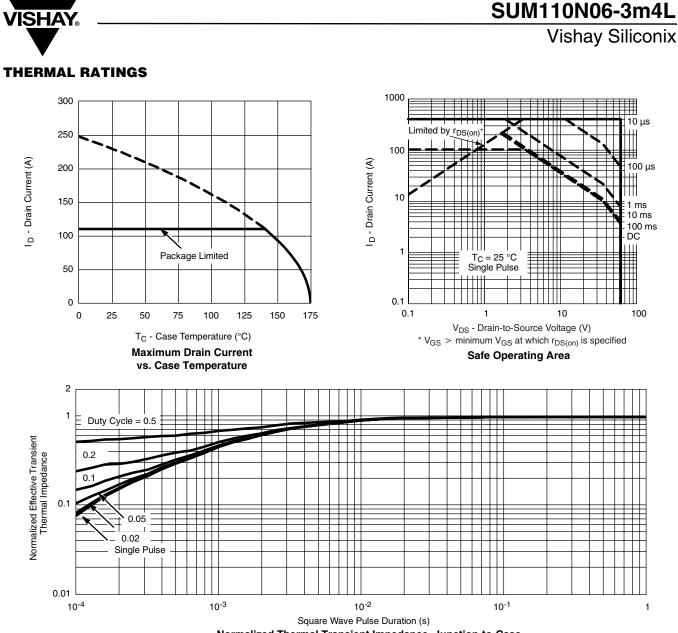
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Normalized Thermal Transient Impedance, Junction-to-Case

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